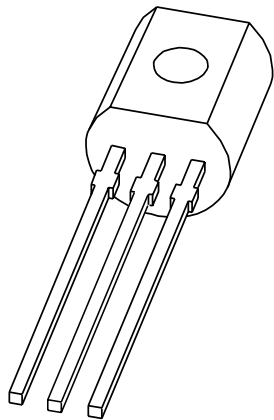


DATA SHEET



PN2907A PNP switching transistor

Product specification
Supersedes data of 1997 May 05

2004 Oct 11

PNP switching transistor

PN2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

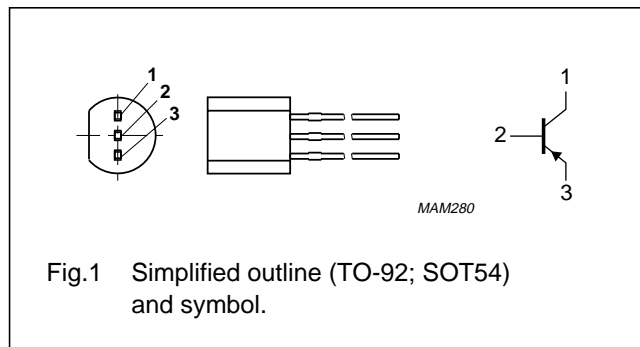
- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a TO-92; SOT54 plastic package. NPN complement: PN2222A.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
I_C	collector current (DC)		–	–600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	500	mW
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}; I_C = -150\text{ mA}$	100	300	
f_T	transition frequency	$V_{CE} = -20\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	200	–	MHz
t_{off}	turn-off time	$I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA}; I_{Boff} = 15\text{ mA}$	–	365	ns

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PN2907A	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

PNP switching transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

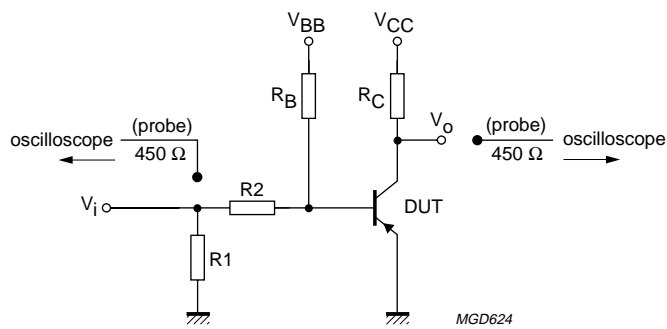
CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0\text{ A}$	–	–10	nA
		$V_{CB} = -50\text{ V}; I_E = 0\text{ A}; T_j = 125\text{ °C}$	–	–10	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}; I_C = -0.1\text{ mA}$	75	–	
		$V_{CE} = -10\text{ V}; I_C = -1\text{ mA}$	100	–	
		$V_{CE} = -10\text{ V}; I_C = -10\text{ mA}$	100	–	
		$V_{CE} = -10\text{ V}; I_C = -150\text{ mA}$	100	300	
		$V_{CE} = -10\text{ V}; I_C = -500\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–400	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–1.3	V
		$I_C = -150\text{ mA}; I_B = -50\text{ mA}$	–	–2.6	V
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$V_{EB} = -2\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$V_{CE} = -20\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	200	–	MHz

PNP switching transistor

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Switching times (between 10 % and 90 % levels); see Fig.2					
t_{on}	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$ $I_{Boff} = 15 \text{ mA}$	–	40	ns
t_d	delay time		–	12	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	365	ns
t_s	storage time		–	300	ns
t_f	fall time		–	65	ns



$V_i = -9.5 \text{ V}; T = 500 \mu\text{s}; t_p = 10 \mu\text{s}; t_r = t_f \leq 3 \text{ ns}.$
 $R_1 = 68 \Omega; R_2 = 325 \Omega; R_B = 325 \Omega; R_C = 160 \Omega.$
 $V_{BB} = 3.5 \text{ V}; V_{CC} = -29.5 \text{ V}.$
 Oscilloscope: input impedance $Z_i = 50 \Omega.$

Fig.2 Test circuit for switching times.

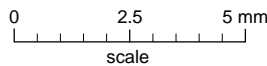
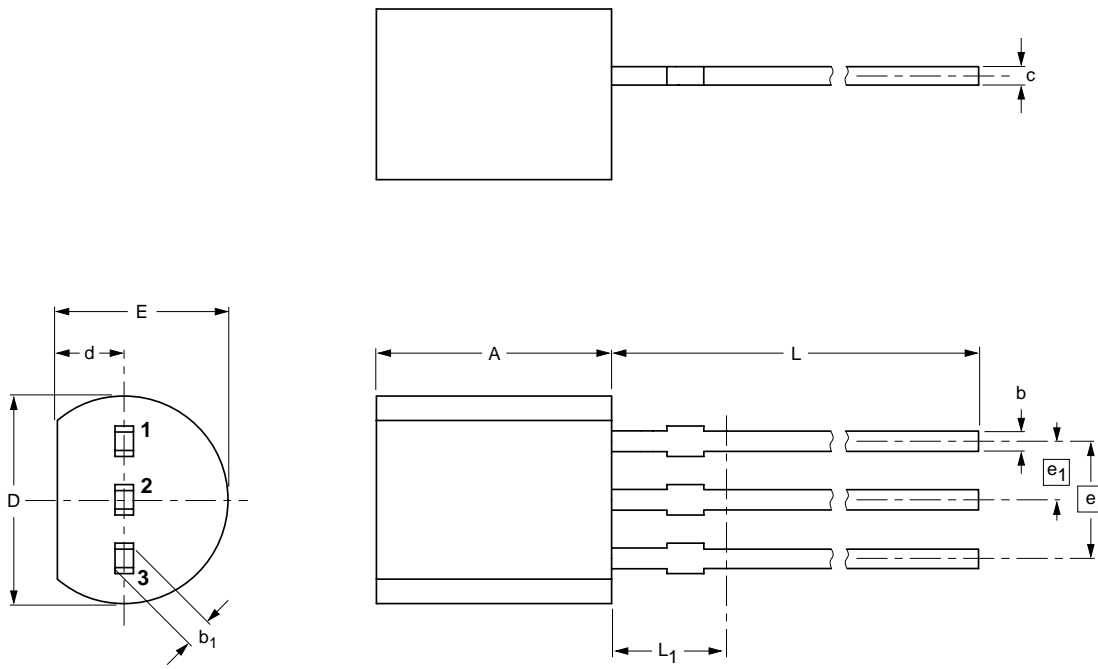
PNP switching transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		-97-02-28 04-06-28

PNP switching transistor

PN2907A

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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